



CHENMKO ENTERPRISE CO.,LTD

SURFACE MOUNT

Halogens free devices

Power Management (Dual Transistor)

Tr1: VOLTAGE 50 Volts CURRENT 150 mAmpere

DTr2: VOLTAGE 50 Volts CURRENT 50 mAmpere

CHEMF23GP

APPLICATION

* Power management circuit

FEATURE

- * Small surface mounting type. (SOT-563)
- * Power switching circuit in a single package.
- * Mounting cost and area can be cut in half.
- * Both the 2SA1774 & CHDTC114E in one package.
- * Built in bias resistor(R1=10kΩ, Typ.)

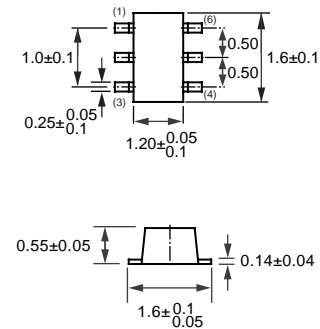
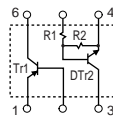
MARKING

* FG



SOT-563

CIRCUIT



SOT-563

2SA1774 LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	Collector-base voltage		–	-60	V
V _{CEO}	Collector-emitter voltage		–	-50	V
V _{EBO}	Emitter-base voltage		–	-6	V
I _c	DC Output current		–	-150	mA
P _c	Total power dissipation	NOTE.1	–	150	mW
T _{STG}	Storage temperature		-55	+150	°C
T _J	Junction temperature		–	150	°C

Note

1. 120mW per element must not be exceeded.

CHDTC114E LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CC}	Supply voltage		-	50	V
V _{IN}	Input voltage		-10	+40	V
I _O	DC Output current		-	50	mA
I _{C(Max.)}		NOTE.1	-	100	
P _C	Power dissipation	NOTE.2	-	150	mW
T _{STG}	Storage temperature		-55	+150	°C
T _J	Junction temperature		-	150	°C

Note

1. Characteristics of built-in transistor.
2. 120mW per element must not be exceeded.
Each terminal mounter on a recommended land.

2SA1774 CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specided.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
BV _{CEO}	Collector-emitter breakdown voltage	I _C =-50uA	-60	-	-	V
BV _{CBO}	Collector-base breakdown voltage	I _C =-1mA	-50	-	-	V
BV _{EBO}	Emitter-base breakdown voltage	I _E =-50uA	-6	-	-	V
I _{CBO}	Collector cut-off current	V _{CB} =-60V	-	-	-100	nA
I _{EBO}	Emitter cut-off current	V _{EB} =-6V	-	-	-100	nA
h _{FE}	DC current gain	V _{CE} =-6V, I _C =-1mA	180	-	390	-
V _{CE(sat)}	Collector-emitter saturation voltage	I _C =-50mA, I _B =-5mA	-	-	-500	mV
C _{ob}	Collector output capacitance	V _{CB} =-12V, I _E =0mA, f=1MHZ	-	4	5	pF
f _T	Transition frequency	V _{CE} =-12V, I _E =2mA, f=100MHZ	-	140	-	MHz

Note

1. Pulse test: t_p≤300uS; δ≤0.02.

CHDTC114E CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specided.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _{I(off)}	Input off voltage	I _O =100uA; V _{CC} =5.0V	0.5	-	-	V
V _{I(on)}	Input on voltage	I _O =10mA; V _O =0.3V	-	-	3.0	V
V _{O(on)}	Output voltage	I _O =10mA; I _I =0.5mA	-	0.1	0.3	V
I _I	Input current	V _I =5V	-	-	0.88	mA
I _{C(off)}	Output current	V _I =0V; V _{CC} =50V	-	-	0.5	uA
G ₁	DC current gain	I _O =5mA; V _O =5.0V	30	-	-	-
R ₁	Input resistor		7	10	13	KΩ
R _{2/R₁}	Resistor ratio		0.8	1.0	1.2	-
f _T	Transition frequency	I _E =-5mA, V _{CE} =10.0V f=100MHz	-	250	-	MHz

Note

- Pulse test: t_p≤300uS; δ≤0.02.

RATING CHARACTERISTIC CURVES (CHEMF23GP)

2SA1774 Typical Electrical Characteristics

Fig.1 Grounded emitter propagation characteristics

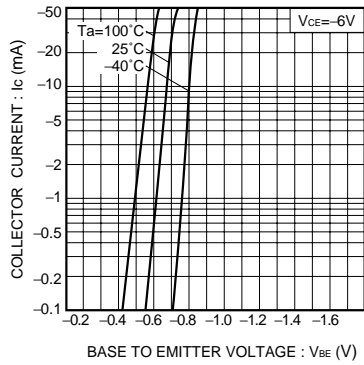


Fig.2 Grounded emitter output characteristics (1)

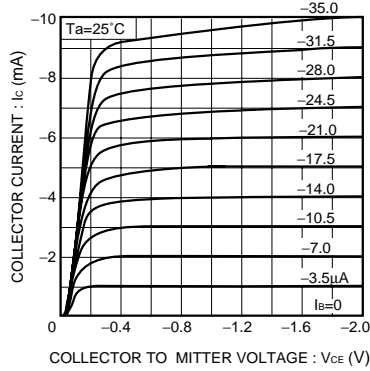


Fig.3 Grounded emitter output characteristics (2)

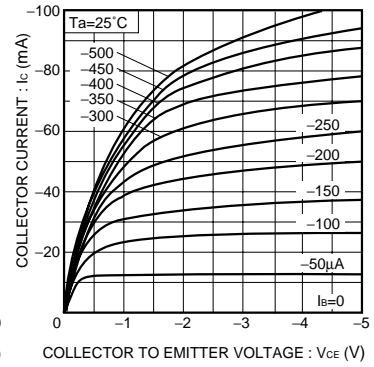


Fig.4 Collector-emitter saturation voltage vs. collector current

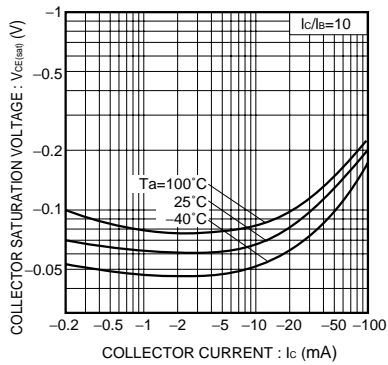


Fig.5 DC current gain vs. collector current

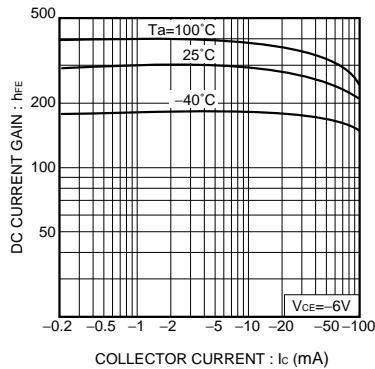
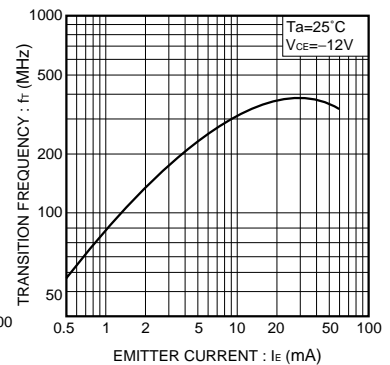


Fig.6 Gain bandwidth product vs. emitter current



RATING CHARACTERISTIC CURVES (CHEMF23GP)

CHDTC114E Typical Electrical Characteristics

Fig.1 Input voltage vs. output current (ON characteristics)

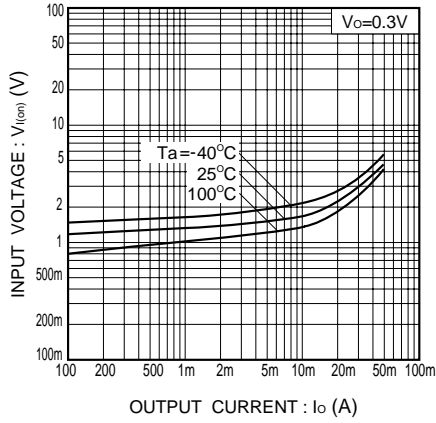


Fig.2 Output current vs. input voltage (OFF characteristics)

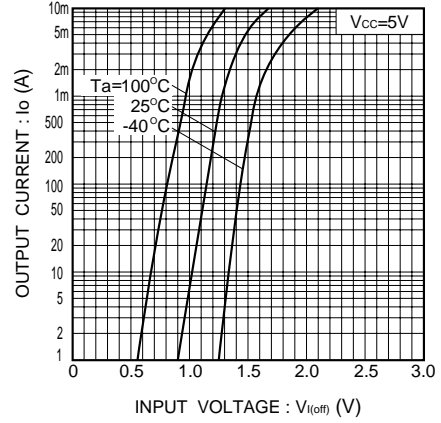


Fig.3 DC current gain vs. output current

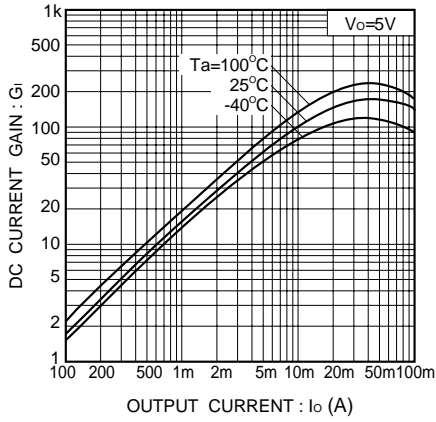


Fig.4 Output voltage vs. output current

